

SEMICONDUCTOR

KSP8598/8599

- Amplifier Transistor Collector-Emitter Voltage: V_{CEO}= KSP8598: 60V
- KSP8599: 80V
- Collector Power Dissipation: P_C (max)=625mW
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)

PNP Epitaxial Silicon Transistor



KSP8598/8599

1. Emitter 2. Base 3. Collector

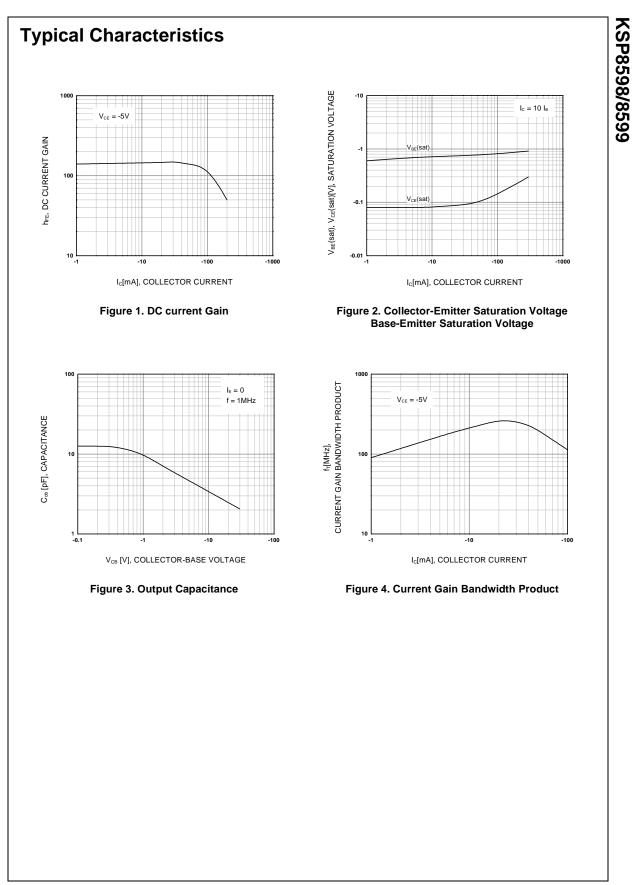
Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage			
	: KSP8598	-60	V	
	: KSP8599	-80	V	
V _{CEO}	Collector-Emitter Voltage			
	: KSP8598	-60	V	
	: KSP8599	-80	V	
V _{EBO}	Emitter-Base Voltage	-5	V	
I _C	Collector Current	-500	mA	
P _C	Collector Power Dissipation	625	mW	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	-55 ~ 150	°C	

Electrical Characteristics Ta=25°C unless otherwise noted

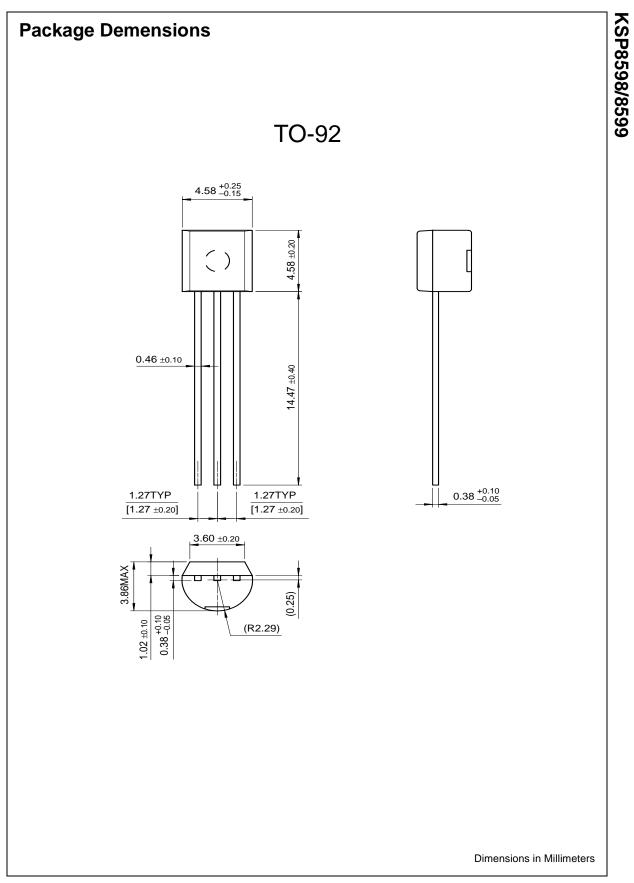
Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = -100μA, I _E =0			
	: KSP8598		-60		V
	: KSP8599		-80		V
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C = -10mA, I _B =0			
	: KSP8598		-60		V
	: KSP8599		-80		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = -10μΑ, I _C =0	-5		V
I _{CBO}	Collector Cut-off Current				
	: KSP8598	V _{CB} = -60V, I _E =0		-100	nA
	: KSP8599	V _{CB} = -80V, I _E =0		-100	nA
I _{CEO}	Collector Cut-off Current	V _{CE} = -60V, I _B =0		-100	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} = -4V, I _C =0		-100	nA
h _{FE}	* DC Current Gain	V _{CE} = -5V, I _C = -1mA	100	300	
		V _{CE} = -5V, I _C = -10mA	100		
		V _{CE} = -5V, I _C = -100mA	75		
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C = -100mA, I _B = -5mA		-0.4	V
		I _C = -100mA, I _B = -10mA		-0.3	V
V _{BE} (on)	* Base-Emitter On Voltage				
	: KSP8598	V _{CE} = -5V, I _C = -1mA	-0.5	-0.7	V
	: KSP8599	V _{CE} = -5V, I _C = -10mA	-0.6	-0.8	V
f _T	Current Gain Bandwidth Product	V _{CE} = -5V, I _C = -10mA	150		MHz
		f=100MHz			
C _{ob}	Output Capacitance	V _{CB} = -5V, I _E =0		8	pF
		f=1MHz			

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